L Number	Hits	Search Text	DB	Time stamp
4	165	((thin adj film adj transistor) tft) same (cmos complementary) same (channel with (impurit$4 dop$4) with ("p-type" "p type" "p-doped" "p doped" boron))	USPAT; US-PGPUB	2004/06/09 10:24
5	24	((channel with (impurit$4 dop$4) with ("p-type" "p type" "p-doped" "p doped" boron))) and ((thin adj film adj transistor) tft) and (cmos complementary)	EPO; JPO; DERWENT; IBM_TDB	2004/06/09 12:27
6	122	(((channel near4 (impurit$4 dop$4)) with ("p-type" "p type" "p-doped" "p doped" boron))) same ((thin adj film adj transistor) tft cmos complementary)	EPO; JPO; DERWENT; IBM_TDB	2004/06/09 12:42
7	82	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls. 345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and ((thin adj film adj transistor) tft) and ((cmos complementary) same (channel with (impurit$4 dop$4) with ("p-type" "p type" "p-doped" "p doped" boron)))	USPAT; US-PGPUB	2004/06/09 13:11
-	12	6635521.pn. 5403764.pn. 5563427.pn. 5643826.pn. 5751037.pn. 5824573.pn. 5885861.pn. 6001677.pn. 6033944.pn. 6127210.pn. 6168980.pn. 6380016.pn.	USPAT; US-PGPUB	2004/06/08 10:49
-	4	jp-10079517-$.did. jp-02023651-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/04 16:05
-	4771	((thin adj film adj transistor) tft) same (cmos nmos pmos complementary "p-type" "n-type")	USPAT; US-PGPUB	2004/06/08 11:00
-	936	((thin adj film adj transistor) tft) same (cmos complementary) same (channel with ("p-type" "p-doped" type dop$4))	USPAT; US-PGPUB	2004/06/08 17:38
-	575	((thin adj film adj transistor) tft) same ((cmos complementary) with (channel near4 ("p-type" "p-doped" type dop$4)))	USPAT; US-PGPUB	2004/06/08 17:17
-	169	(((thin adj film adj transistor) tft) same (cmos complementary) same (channel with ("p-type" "p-doped" type dop$4))) same ((impurit$4 dop$4 boron "p-type" "p type") near4 concentration)	USPAT; US-PGPUB	2004/06/08 11:11
-	0	6632711.URPN.	USPAT	2004/06/08 13:01
-	0	6635521.URPN.	USPAT	2004/06/08 13:01
-	139	((thin adj film adj transistor) tft) and (cmos complementary) and (channel with ("p-type" "p-doped" type dop$4))	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 17:46
-	2	jp-09186343-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/08 17:15
-	3951	257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls. 345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.	USPAT; US-PGPUB	2004/06/08 17:16
-	393	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls. 345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and ((thin adj film adj transistor) tft) and ((cmos complementary) same (channel with ("p-type" "p-doped" type dop$4)))	USPAT; US-PGPUB	2004/06/08 17:19
-	106	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls. 345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and ((thin adj film adj transistor) tft) and ((cmos complementary) same (channel near4 ("p-type" "p-doped" dop$4)))	USPAT; US-PGPUB	2004/06/08 17:26
-	938	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls. 345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and (channel with (impurit$4 dop$4) with ("p-type" "p type" "p-doped" "p doped" boron))	USPAT; US-PGPUB	2004/06/08 17:44
-	180	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls. 345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and ((cmos complementary) same (channel with (impurit$4 dop$4) with ("p-type" "p type" "p-doped" "p doped" boron)))	USPAT; US-PGPUB	2004/06/08 17:42

-	447	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls. 345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and ((thin adj film adj transistor) tft) and (cmos complementary) and (channel with (impurit$4 dop$4) with ("p-type" "p type" "p-doped" "p doped" boron))	USPAT; US-PGPUB	2004/06/08 17:43
-	2243	(channel with (impurit$4 dop$4) with ("p-type" "p type" "p-doped" "p doped" boron))	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 17:47
-	533	((channel with (impurit$4 dop$4) with ("p-type" "p type" "p-doped" "p doped" boron))) and ((thin adj film adj transistor) tft cmos complementary)	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 17:48
-	884	((channel near4 (impurit$4 dop$4)) with ("p-type" "p type" "p-doped" "p doped" boron))	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 17:47
-	222	(((channel near4 (impurit$4 dop$4)) with ("p-type" "p type" "p-doped" "p doped" boron))) and ((thin adj film adj transistor) tft cmos complementary)	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 17:48